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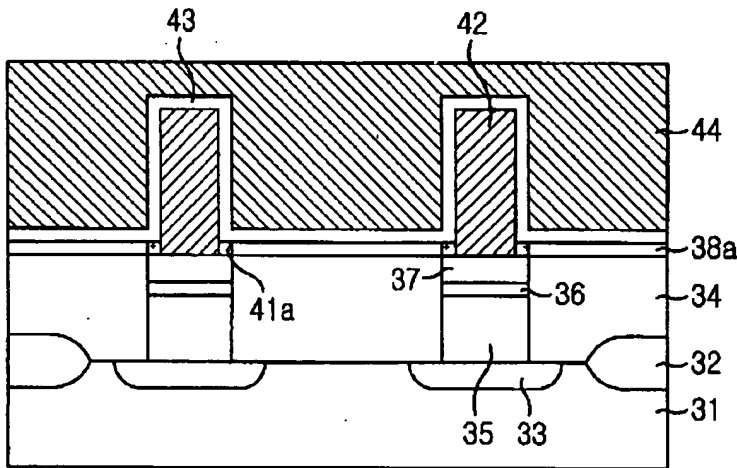
METHOD FOR MANUFACTURING CAPACITOR

Representative drawing

(57) Abstract:

PURPOSE: A method for manufacturing a capacitor is provided to be capable of preventing attacks of an interlayer dielectric due to etchants when wet-etching of a capacitor oxide layer.

CONSTITUTION: An interlayer dielectric(34) having a storage node contact(35) is formed on a semiconductor substrate(31). The first etch stop layer(38a), the second etch stop layer and a sacrificial layer as a capacitor oxide layer are sequentially formed on the interlayer dielectric. A concave pattern is formed to expose the storage node contact(35) by sequentially etching the sacrificial layer and the second and first etch stop layer. The third etch stop layer is formed at inner walls of the concave pattern. A lower electrode(42) is filled into the concave pattern. The sacrificial layer is removed by wet-etching. By selectively removing the third and second etch stop layer, an oxide barrier layer(41a) made of the third etch stop layer remains to contact the both sidewalls of the lower electrode(42). A dielectric film(43) and an upper electrode(44) are sequentially formed on the lower electrode.



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